CLAIMS

1. A method of reproducing a mark on a semiconductor wafer, wherein, in a case where a predetermined mark which has been made on a semiconductor wafer beforehand during the course of manufacture or processing is substantially effaced in association with progress of manufacturing operation or processing operation, a mark essentially identical with the substantially-effaced mark is formed at another location spaced apart from the substantially-effaced mark.

2. A method of reproducing a mark on a semiconductor wafer, wherein, in a case where any one of predetermined single essentially-identical marks which have been made in two or more locations on a semiconductor wafer beforehand during the course of manufacture or processing is substantially effaced in association with progress of manufacturing operation or processing operation, a mark essentially identical with the substantially-effaced mark is reproduced by reference to the substantially-remaining other mark.

3. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location spaced apart from the substantially-effaced mark.

4. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the substantially-effaced mark is reproduced by means of forming a mark essentially identical

with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

5. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is formed by means of a combination of dots, each dot measuring 1 to 13 μm, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

6. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is a minute ID mark which is assigned to the semiconductor wafer and is formed by means of a combination of dots, each dot measuring 1 to 13 μm, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

7. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is a mark affixed on the interior wall surface of a notch.

8. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is a mark affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location spaced apart from the substantially-effaced mark.

9. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is a mark affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

Sub B1

10. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is formed by means of a combination of dots, each dot measuring 1 to 13 μm and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

Sub A2

11. The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is an ID mark which is assigned to the semiconductor wafer, is formed by means of a combination of dots, each dot measuring 1 to 13 μm, and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

12. A semiconductor wafer for distribution purpose having two or more essentially identical marks formed thereon.

Sub B1

13. The semiconductor wafer for distribution purpose

according to claim 12, wherein two or more essentially-identical marks are provided at positions where the marks are to undergo the same surface treatment at different speeds during the course of manufacture.

14. The semiconductor wafer for distribution purpose according to claim 12, wherein some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture.

15. The semiconductor wafer for distribution purpose according to claim 12, wherein some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks are located close to each other and such that the marks undergo the same surface treatment at different speeds during the course of manufacture.

16. The semiconductor wafer for distribution purpose according to claim 12, wherein some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read

the marks simultaneously.

17. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 µm, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

18. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the semiconductor wafer and are formed by means of a combination of dots, each dot measuring 1 to 13 µm, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

19. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the semiconductor

wafer, are formed by means of a combination of dots, each dot measuring 1 to 13 μm, and are affixed on the interior wall surface of a notch, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

20. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 μm for positioning purpose, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

21. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 μm and indicate crystal orientation of the semiconductor wafer, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks

are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

22. The semiconductor wafer for distribution purpose according to claim 12, wherein the semiconductor wafer is perfectly annular; two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 μm and indicate crystal orientation of the semiconductor wafer; and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

23. The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are aligned in a single direction; and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

Sub B1

24. Use of a semiconductor wafer on which two or more essentially-identical marks are formed by means of marking the semiconductor wafer during the course of manufacture or processing.

25. A method of obviating a demerit, which would otherwise be caused when a single mark is substantially effaced in association with manufacture or processing of a semiconductor wafer, by means of marking a semiconductor wafer with two or more essentially-identical marks during the course of manufacture or processing.